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PMEG050V150EPD

50 V, 15 A low VF MEGA Schottky barrier rectifier

4 December 2014

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 15 \text{ A}$
- Reverse voltage: $V_R \leq 50 \text{ V}$
- Extremely low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20 \text{ kHz}$; $T_{sp} \leq 160 \text{ }^\circ\text{C}$; square wave	-	-	15	A
V_R	reverse voltage	$T_j = 25 \text{ }^\circ\text{C}$	-	-	50	V
V_F	forward voltage	$I_F = 15 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	450	500	mV
I_R	reverse current	$V_R = 10 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	30	70	μA
		$V_R = 50 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	260	1000	μA



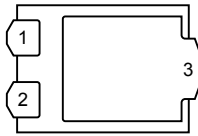
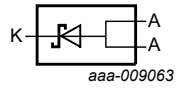
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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 CFP15 (SOT1289)	 aaa-009063
2	A	anode		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG050V150EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG050V150EPD	050V 150E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^\circ\text{C}$		-	50	V
I_F	forward current	$T_{sp} = 155\text{ }^\circ\text{C}$; $\delta = 1$		-	21	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 160\text{ }^\circ\text{C}$; square wave		-	15	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; square wave		-	240	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
T_j	junction temperature			-	175	$^\circ\text{C}$
T_{amb}	ambient temperature			-55	175	$^\circ\text{C}$

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Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	175	°C

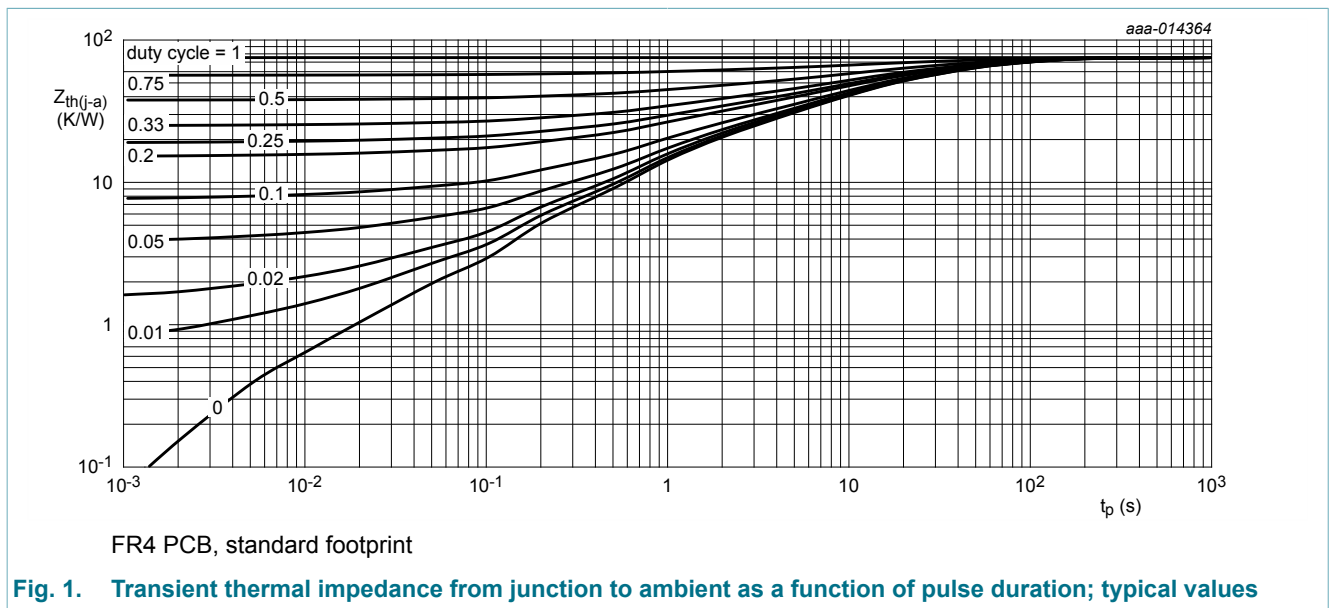
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	90	K/W
			[1][3]	-	70	K/W
			[1][4]	-	40	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	3	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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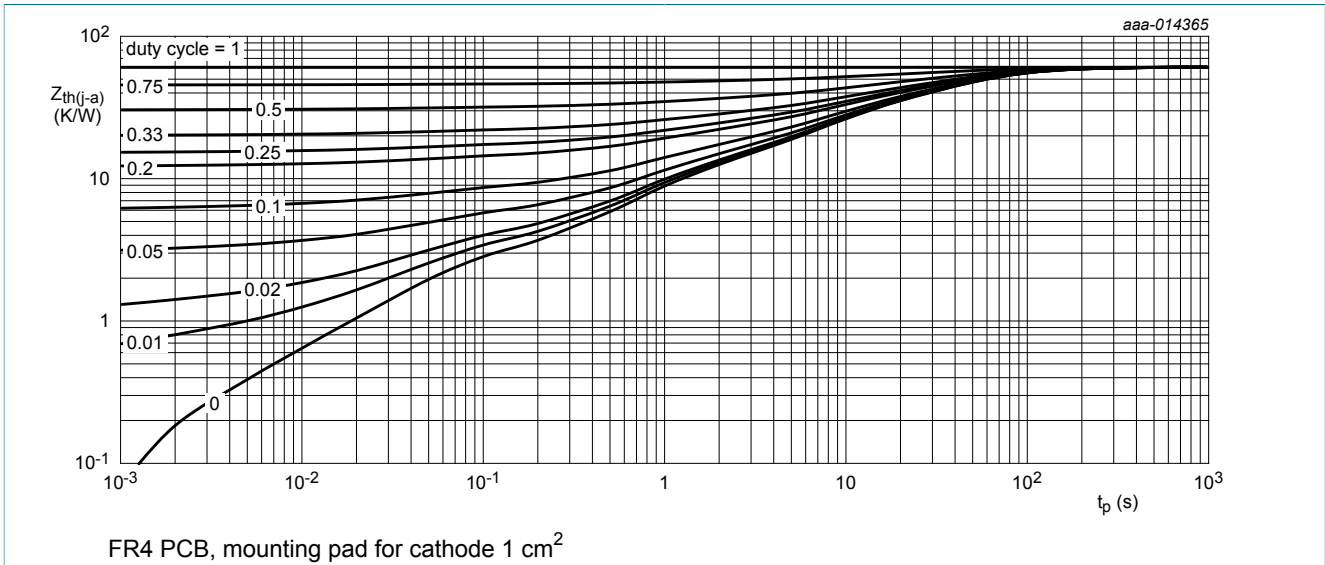


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

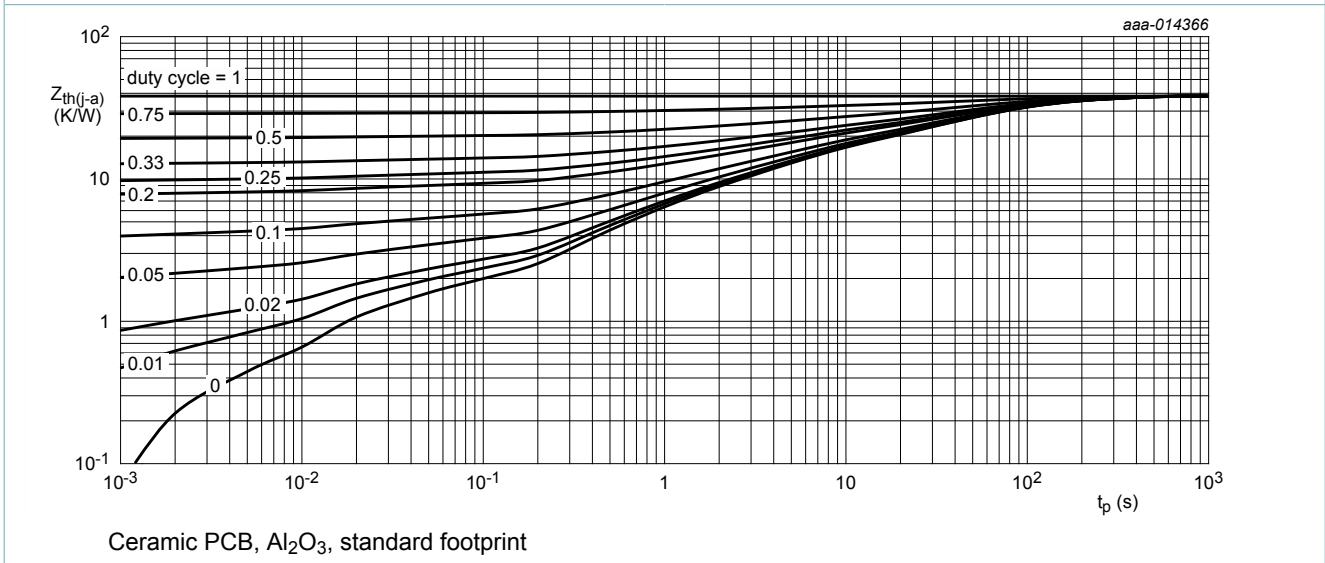
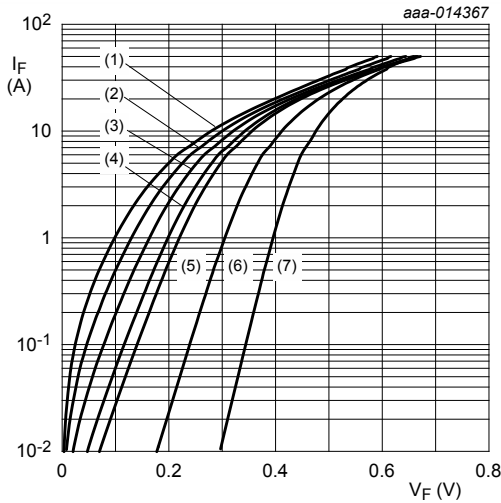


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

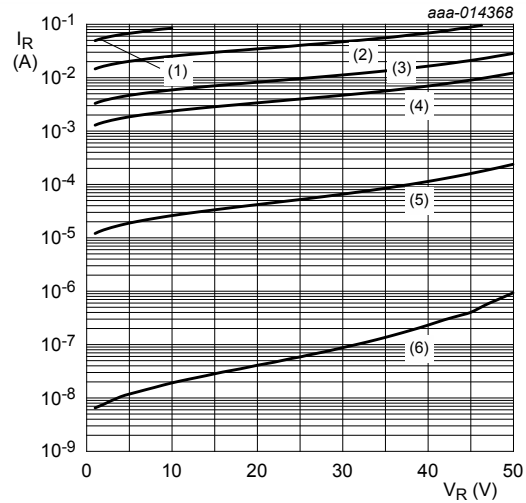
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 5 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$; $t_p \leq 1.2 \text{ ms}$; $\delta \leq 0.12$; pulsed	50	-	-	V
V_F	forward voltage	$I_F = 1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	305	350	mV
		$I_F = 5 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	365	420	mV
		$I_F = 10 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	415	-	mV
		$I_F = 15 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	450	500	mV
		$I_F = 15 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 125 \text{ }^\circ\text{C}$; pulsed	-	380	-	mV
I_R	reverse current	$V_R = 5 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	20	-	μA
		$V_R = 10 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	30	70	μA
		$V_R = 30 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	70	-	μA
		$V_R = 50 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.3$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	-	260	1000	μA
C_d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	1750	-	pF
		$V_R = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	570	-	pF
t_{rr}	reverse recovery time step recovery	$I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(\text{meas})} = 0.1 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$	-	51	-	ns
t_{rr}	reverse recovery time ramp recovery	$dl_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ }^\circ\text{C}$; $I_F = 6 \text{ A}$; $V_R = 26 \text{ V}$	-	20	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}$; $dl_F/dt = 20 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ }^\circ\text{C}$	-	288	-	mV



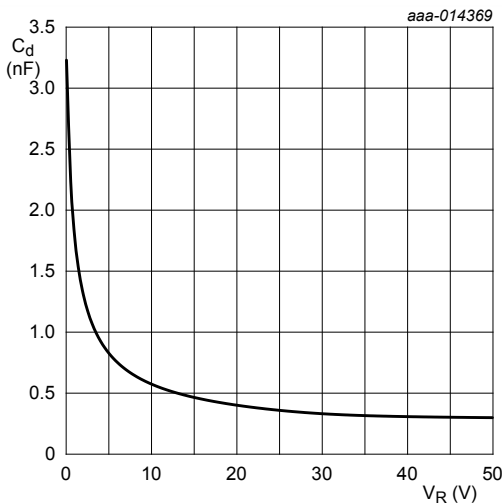
- pulsed condition
- (1) $T_j = 175\text{ }^\circ\text{C}$
 - (2) $T_j = 150\text{ }^\circ\text{C}$
 - (3) $T_j = 125\text{ }^\circ\text{C}$
 - (4) $T_j = 100\text{ }^\circ\text{C}$
 - (5) $T_j = 85\text{ }^\circ\text{C}$
 - (6) $T_j = 25\text{ }^\circ\text{C}$
 - (7) $T_j = -40\text{ }^\circ\text{C}$

Fig. 4. Forward current as a function of forward voltage; typical values



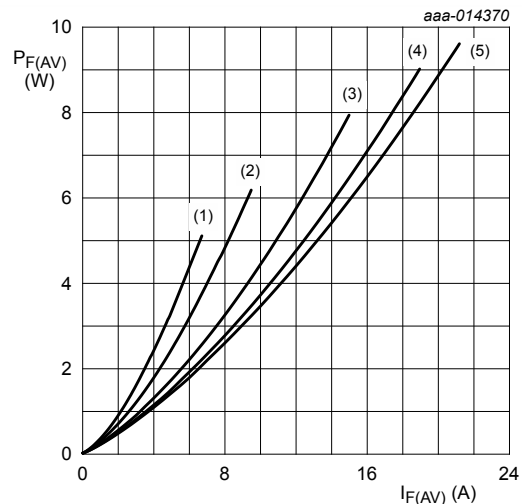
- pulsed condition
- (1) $T_j = 150\text{ }^\circ\text{C}$
 - (2) $T_j = 125\text{ }^\circ\text{C}$
 - (3) $T_j = 100\text{ }^\circ\text{C}$
 - (4) $T_j = 85\text{ }^\circ\text{C}$
 - (5) $T_j = 25\text{ }^\circ\text{C}$
 - (6) $T_j = -40\text{ }^\circ\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



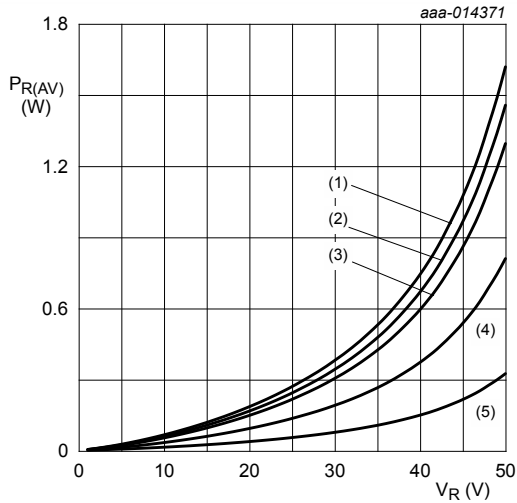
$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



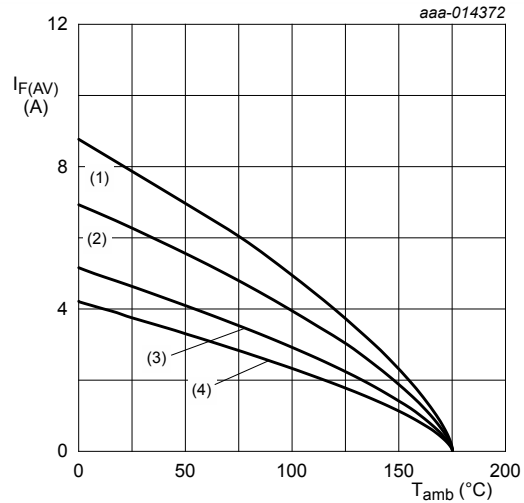
- $T_j = 100\text{ }^\circ\text{C}$
- (1) $\delta = 0.1$
 - (2) $\delta = 0.2$
 - (3) $\delta = 0.5$
 - (4) $\delta = 0.8$
 - (5) $\delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



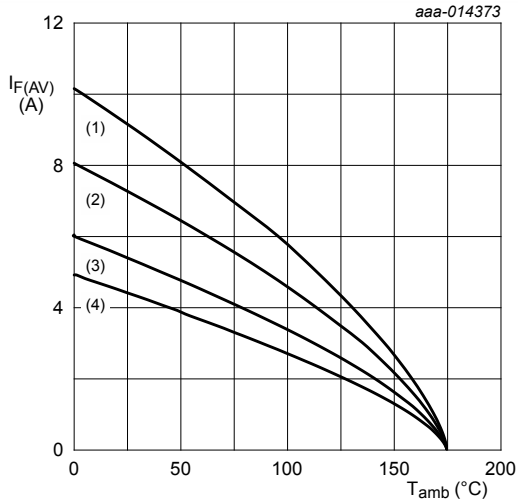
$T_j = 100\text{ °C}$
 (1) $\delta = 1$
 (2) $\delta = 0.9$
 (3) $\delta = 0.8$
 (4) $\delta = 0.5$
 (5) $\delta = 0.2$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



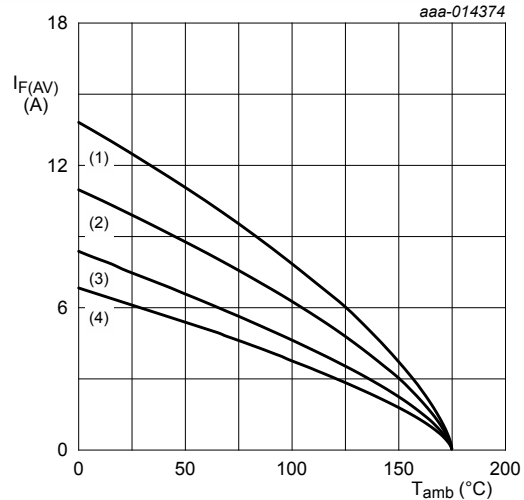
FR4 PCB, standard footprint
 $T_j = 175\text{ °C}$
 (1) $\delta = 1$; DC
 (2) $\delta = 0.5$; $f = 20\text{ kHz}$
 (3) $\delta = 0.2$; $f = 20\text{ kHz}$
 (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 9. Average forward current as a function of ambient temperature; typical values



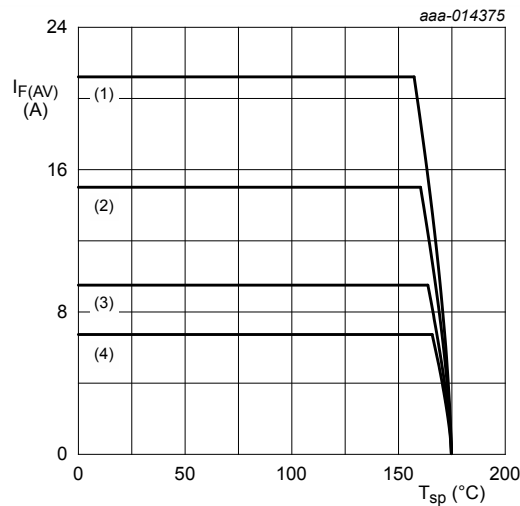
FR4 PCB, mounting pad for cathode 1 cm^2
 $T_j = 175\text{ °C}$
 (1) $\delta = 1$; DC
 (2) $\delta = 0.5$; $f = 20\text{ kHz}$
 (3) $\delta = 0.2$; $f = 20\text{ kHz}$
 (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al_2O_3 , standard footprint
 $T_j = 175\text{ °C}$
 (1) $\delta = 1$; DC
 (2) $\delta = 0.5$; $f = 20\text{ kHz}$
 (3) $\delta = 0.2$; $f = 20\text{ kHz}$
 (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 11. Average forward current as a function of ambient temperature; typical values



$T_j = 175\text{ }^\circ\text{C}$

(1) $\delta = 1$; DC

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 12. Average forward current as a function of solder point temperature; typical values

11. Test information

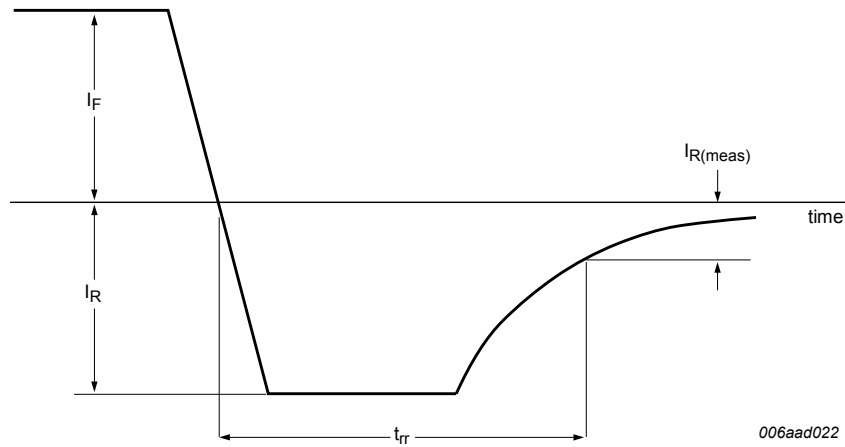


Fig. 13. Reverse recovery definition; step recovery

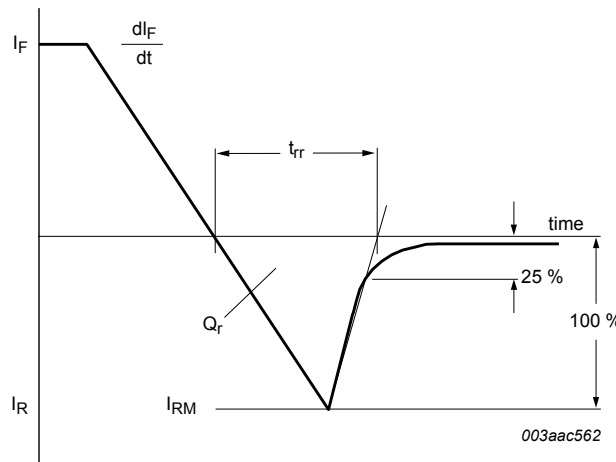


Fig. 14. Reverse recovery definition; ramp recovery

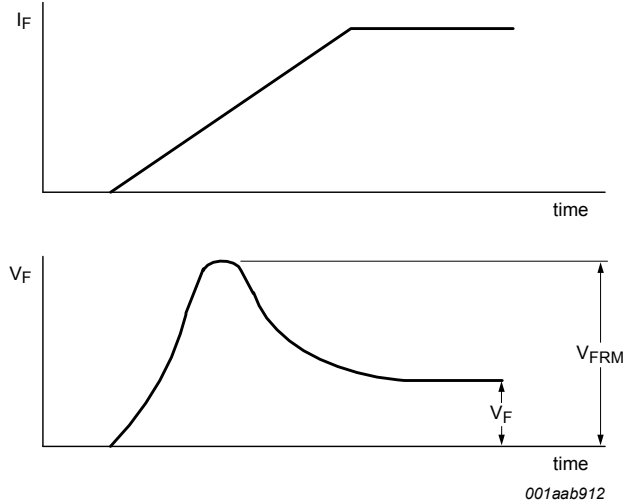


Fig. 15. Forward recovery definition

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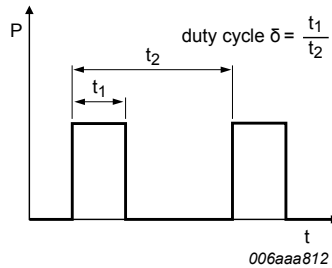


Fig. 16. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:
 $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

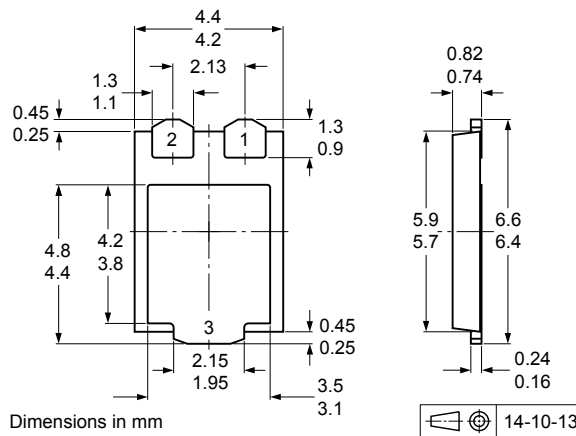


Fig. 17. Package outline CFP15 (SOT1289)

13. Soldering

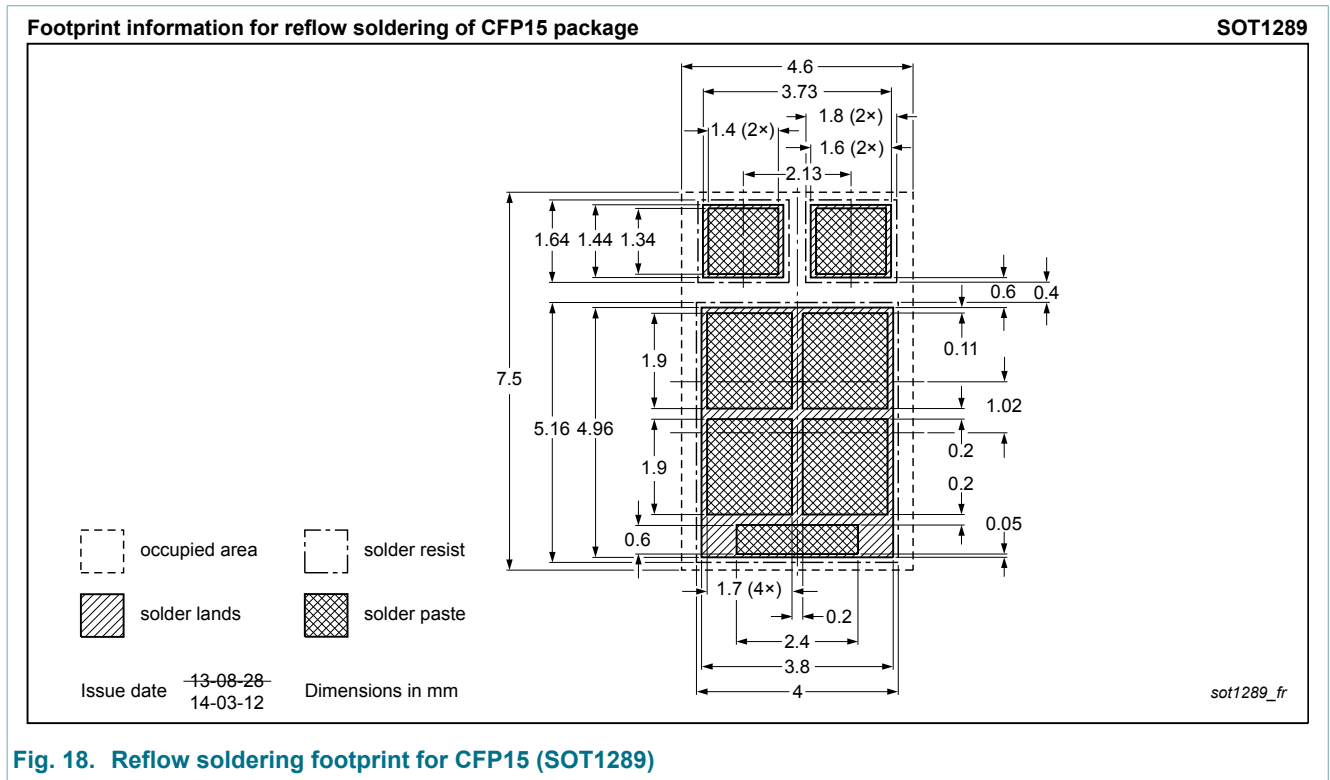


Fig. 18. Reflow soldering footprint for CFP15 (SOT1289)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG050V150EPD v.3	20141204	Product data sheet	-	PMEG050V150EPD v.2
Modifications:	<ul style="list-style-type: none"> Product status changed 			
PMEG050V150EPD v.2	20140704	Preliminary data sheet	-	PMEG050V150EPD v.1
PMEG050V150EPD v.1	20140519	Objective data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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